

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A semiconductor device comprising a field effect transistor formed on a SOI substrate, the semiconductor device characterized in comprising:
- a gate region formed on a semiconductor film of the SOI substrate;
 - source and drain regions each spaced a specified distance from a channel region formed in the semiconductor film below the gate region;
 - a first extension region formed independently of the source region that extends from the source region to the channel region; and
 - a second extension region formed independently of the drain region that extends from the drain region to the channel region,
- wherein junction depths of the first and second extension regions are formed to be shallower than junction depths of the source region and the drain region.
2. (Original) A semiconductor device according to claim 1, wherein the junction depth of each of the first and second extension regions is 50% or less of the junction depth of each of the source region and the drain region.
3. (Original) A semiconductor device according to claim 1 or claim 2 characterized in operating in a fully depleted operation mode.

4. (Original) A semiconductor device according to any one of claim 1 through claim 3, wherein the SOI substrate is a substrate composed of a glass substrate, a quartz substrate or another insulation substrate and a semiconductor film formed thereon.

5-8. (Cancelled)
